TOSHIBA Transistor Silicon NPN Triple Diffused Type (Darlington)

2SD2129

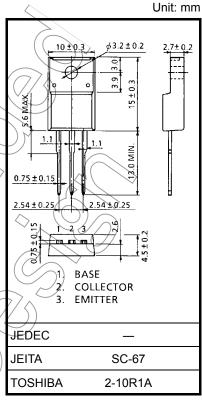
High-Power Switching Applications
Hammer Drive, Pulse Motor Drive Applications

• High DC current gain: hFE = 2000 (min)

• Low saturation voltage: VCE (sat) = 1.5 V (max)

Absolute Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V _{CBO}	100	(/y)
Collector-emitter voltage		V _{CEO}	100	A
Emitter-base voltage		V _{EBO}	7	y
Collector current	DC	Ic	3	\Rightarrow A
	Pulse	I _{CP}	5	• ^
Base current		I _B	0.5	A
Collector power dissipation	Ta = 25°C	PC	2.0	W
	Tc = 25°C		20	~~~
Junction temperature		T _j ((150	°C/
Storage temperature range		Tsfg	-55 to 150	√ °C

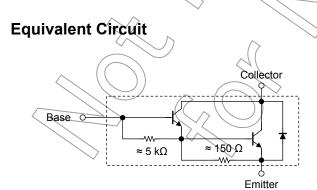


Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

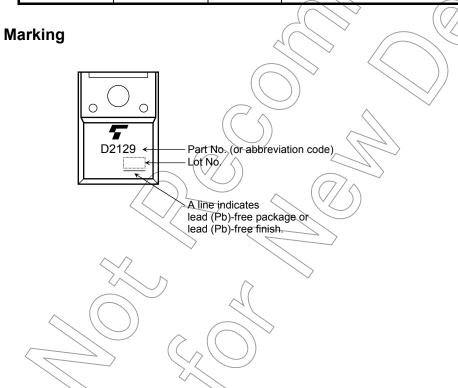
temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

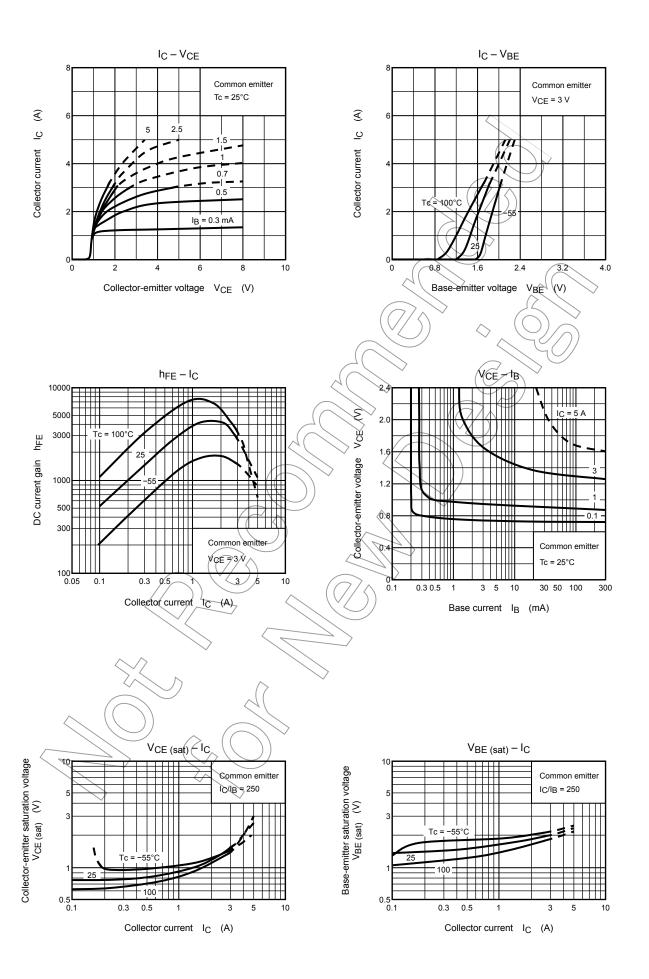


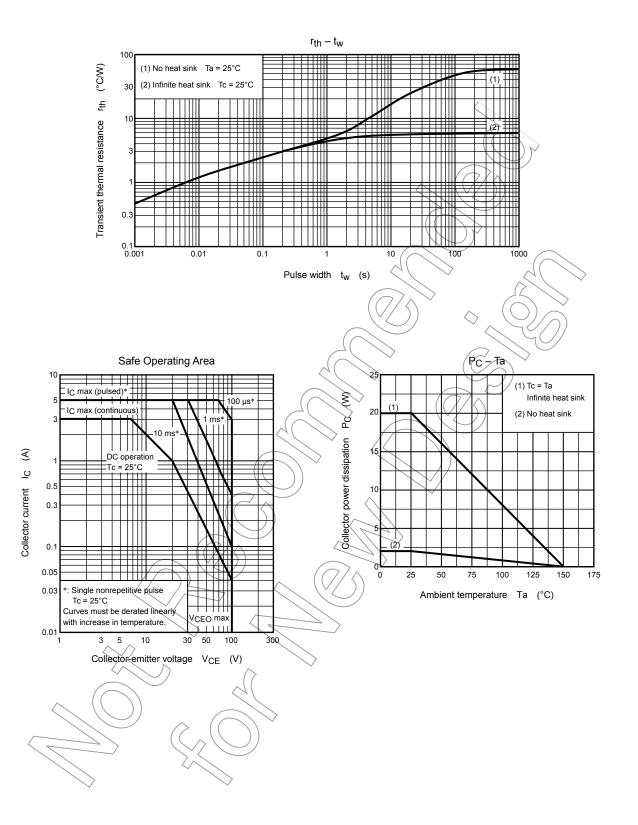
Electrical Characteristics (Tc = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off of	current	I _{CBO}	V _{CB} = 100 V, I _E = 0	_	_	100	μΑ	
Emitter cut-off cu	rrent	I _{EBO}	V _{EB} = 6 V, I _C = 0	_	_	2.5	mA	
Collector-emitter	breakdown voltage	V (BR) CEO	I _C = 30 mA, I _B = 0	100	_	_	V	
DC current gain		h _{FE (1)}	V _{CE} = 3 V, I _C = 1.5 A	2000 — 15000		15000		
		h _{FE (2)}	V _{CE} = 3 V, I _C = 3 A	1000) / _	_		
Collector-emitter saturation voltage		V _{CE} (sat) (1)	I _C = 1.5 A, I _B = 3 mA	>_	_	1.5	V	
		V _{CE} (sat) (2)	I _C = 3 A, I _B = 12 mA	$\bigcirc)$	_	2.0		
Base-emitter saturation voltage V _{BE (sat}		V _{BE} (sat)	I _C = 1.5 A, I _B = 3 mA	_	_	2.0	V	
Switching time Stor	Turn-on time	t _{on}	Input B1 Output	_	1.0	1//	μs	
	Storage time	t _{stg}	20 µs IB2 W VCC ≈ 30 V		5.0	> _		
	Fall time	t _f	I _{B1} = -I _{B2} = 3 mA, duty cycle ≤ 1%					



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